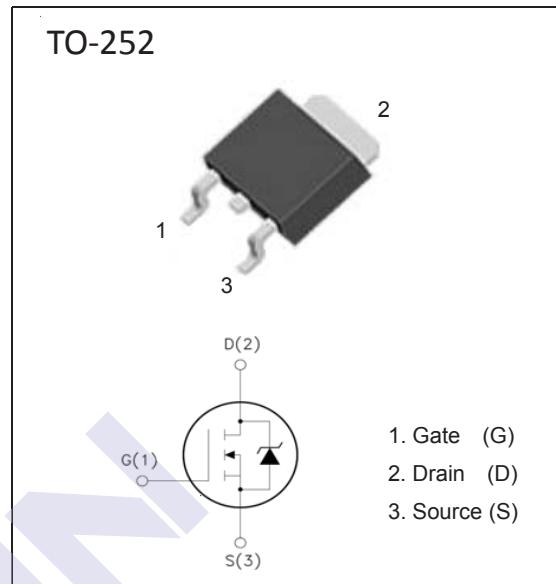


N-Channel MOSFET

2KK5064



■ Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _{GSS}	±20	
Continuous Drain Current	I _D	42	A
		30	
	I _{DM}	140	
Single Pulse Avalanche Energy (Note 2)	E _{AS}	420	mJ
Avalanche Current (Note 1)	I _{AR}	22	A
Repetitive Avalanche Energy (Note 1)	E _{AR}	16	mJ
Peak Diode Recovery (Note 3)	dV/dt	5	V/ns
Thermal Resistance, Junction-to-Ambient	R _{θJA}	40	°C/W
Thermal Resistance, Junction-to-Case	R _{θJC}	0.95	
Maximum Power Dissipation	P _D	3.8	W
		160	
Operating Junction and Storage Temperature Range	T _J , T _{Stg}	-55 to 175	°C

Notes

1. Repetitive rating; pulse width limited by max. junction temperature.
2. Starting T_J = 25°C, L = 1.7mH, R_G = 25Ω, I_{AS} = 22A.
3. I_{SD} ≤ 22A, dV/dt ≤ 180A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 175°C

2KK5064

■ Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	100			V
Zero Gate Voltage Drain Current	I_{DS}	$V_{DS}=100\text{V}, V_{GS}=0\text{V}$			1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{DS}=0\text{V}, V_{GS}=\pm20\text{V}$			±100	nA
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1.3		2.5	V
Static Drain-Source On-Resistance (Note 1)	$R_{DS(\text{ON})}$	$V_{GS}=10\text{V}, I_D=22\text{A}$		42	50	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}, I_D=10\text{A}$		45	58	
Input Capacitance	C_{iss}	$V_{GS}=0\text{V}, V_{DS}=25\text{V}, f=1\text{MHz}$		1900		pF
Output Capacitance	C_{oss}			450		
Reverse Transfer Capacitance	C_{rss}			230		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=50\text{V}, I_D=22\text{A}, R_G=3.6\Omega, R_D=2.9\Omega$		11		ns
Turn-On Rise Time	t_r			56		
Turn-Off Delay Time	$t_{d(off)}$			45		
Turn-Off Fall Time	t_f			40		
Total Gate Charge	Q_g	$V_{DS}=80\text{V}, I_D=22\text{A}, V_{GS}=10\text{V}$			110	nC
Gate Source Charge	Q_{gs}				15	
Gate Drain Charge	Q_{gd}				58	
Body Diode Voltage	V_{SD}	$I_S=22\text{A}, V_{GS}=0\text{V}$			1.3	V
Diode Forward Current	I_S				42	A
Body Diode Reverse Recovery Time	t_{rr}	$V_{GS}=0\text{V}, I_S = 22 \text{ A}, dI/dt = 100 \text{ A}/\mu\text{s}$		180		ns
Body Diode Reverse Recovery Charge	Q_{rr}			1.2		μC

Notes:

1. Pulse Test: Pulse Width $\leqslant 300\mu\text{s}$, Duty Cycle $\leqslant 2\%$.
2. Switching characteristics are independent of operating junction temperature.

■ Marking

Marking	K5064 K****
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2KK5064

■ Typical Characteristics

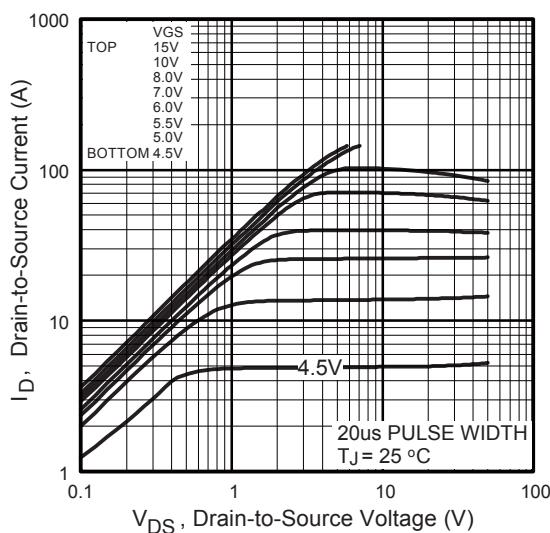


Fig 1. Typical Output Characteristics

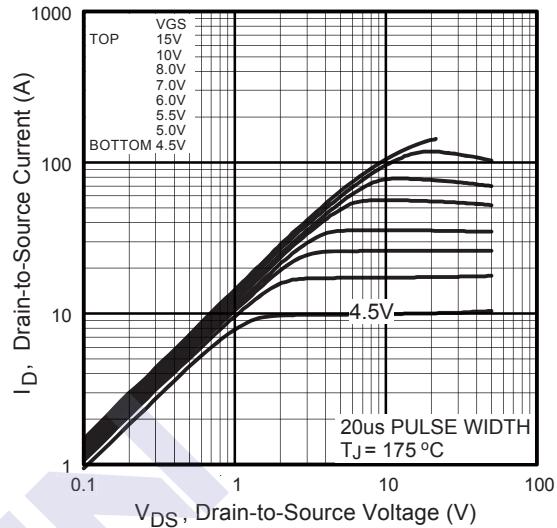


Fig 2. Typical Output Characteristics

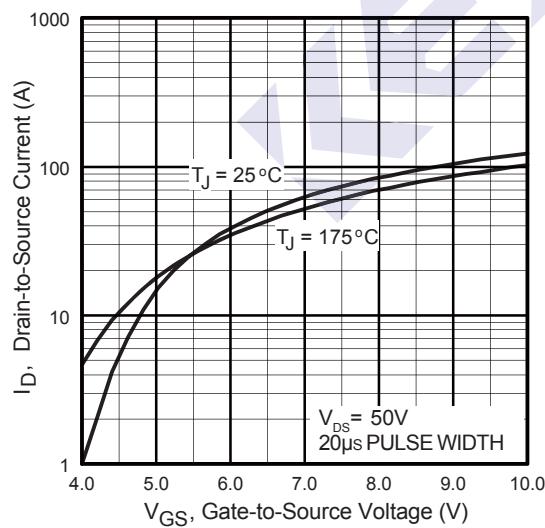


Fig 3. Typical Transfer Characteristics

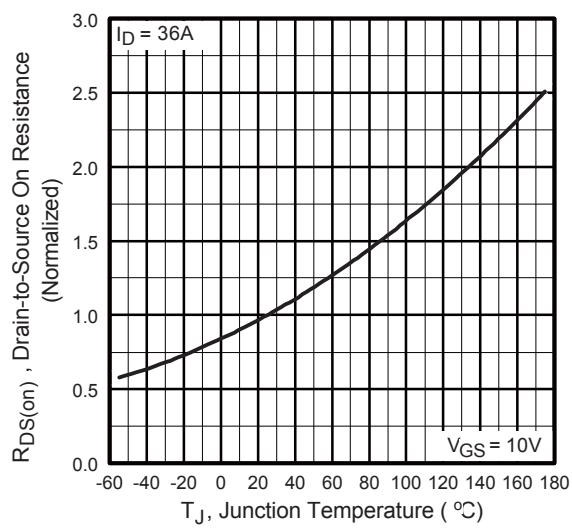


Fig 4. Normalized On-Resistance Vs. Temperature

2KK5064

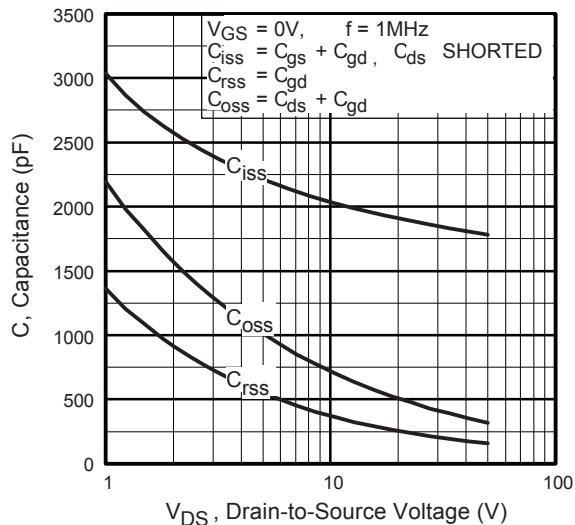


Fig 5. Typical Capacitance Vs.
Drain-to-Source Voltage

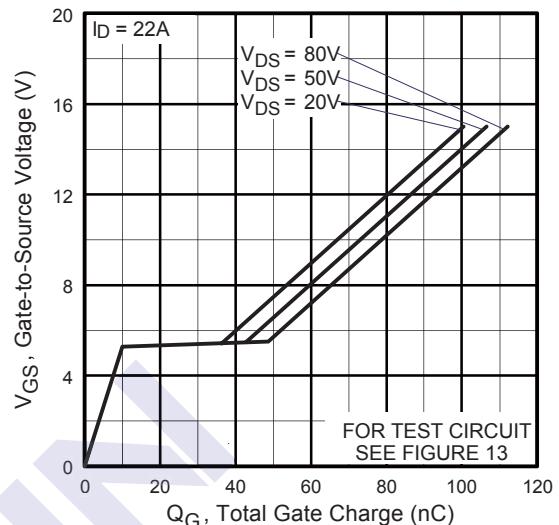


Fig 6. Typical Gate Charge Vs.
Gate-to-Source Voltage

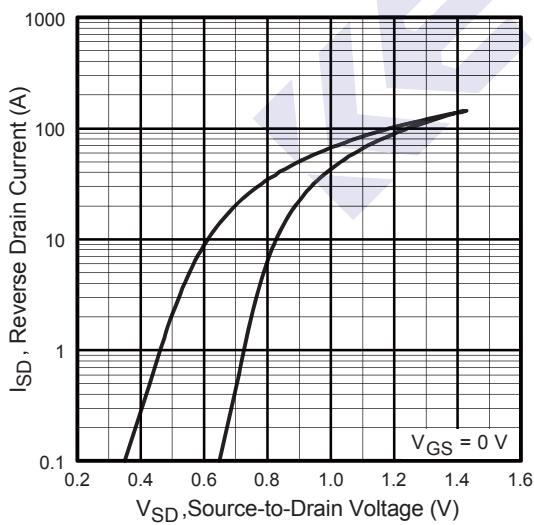


Fig 7. Typical Source-Drain Diode
Forward Voltage

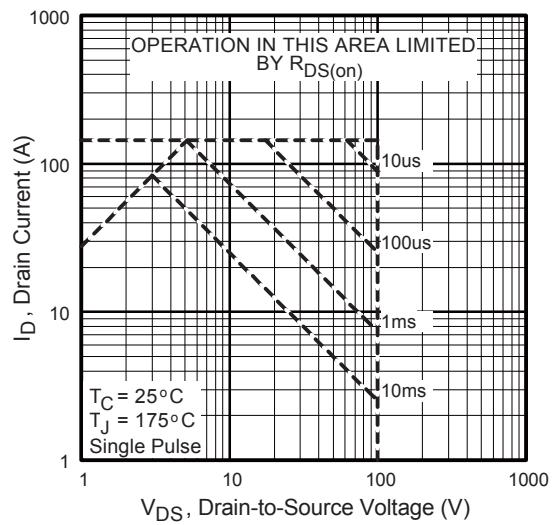


Fig 8. Maximum Safe Operating Area

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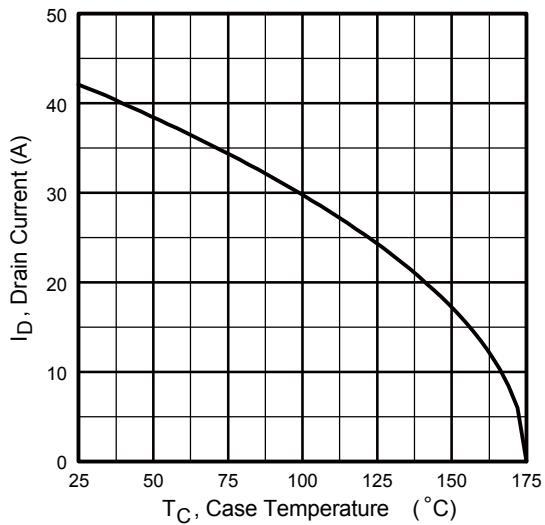


Fig 9. Maximum Drain Current Vs.
Case Temperature

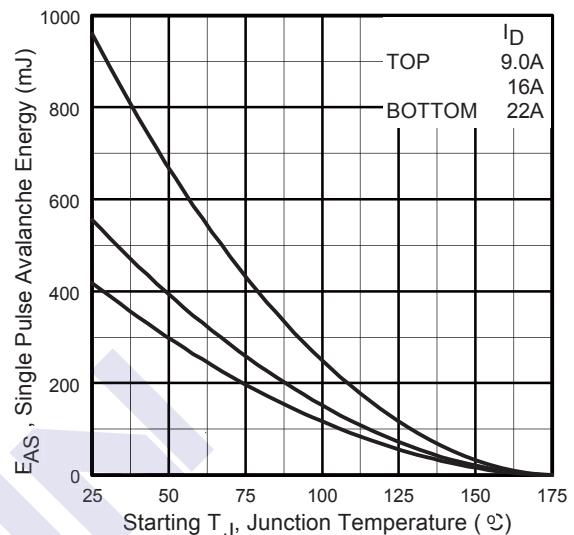


Fig 10. Maximum Avalanche Energy
Vs. Drain Current

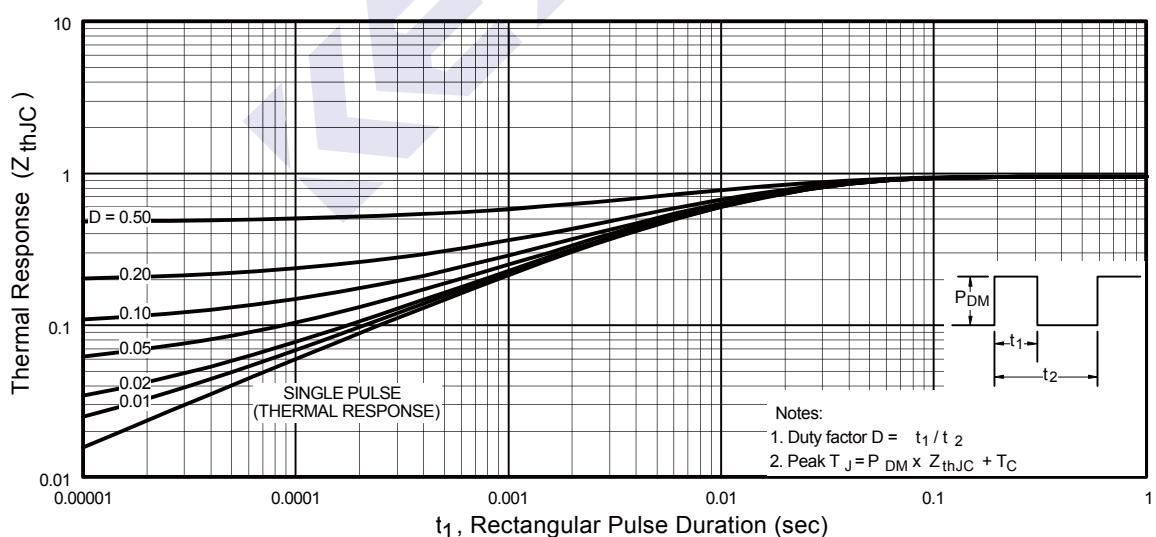


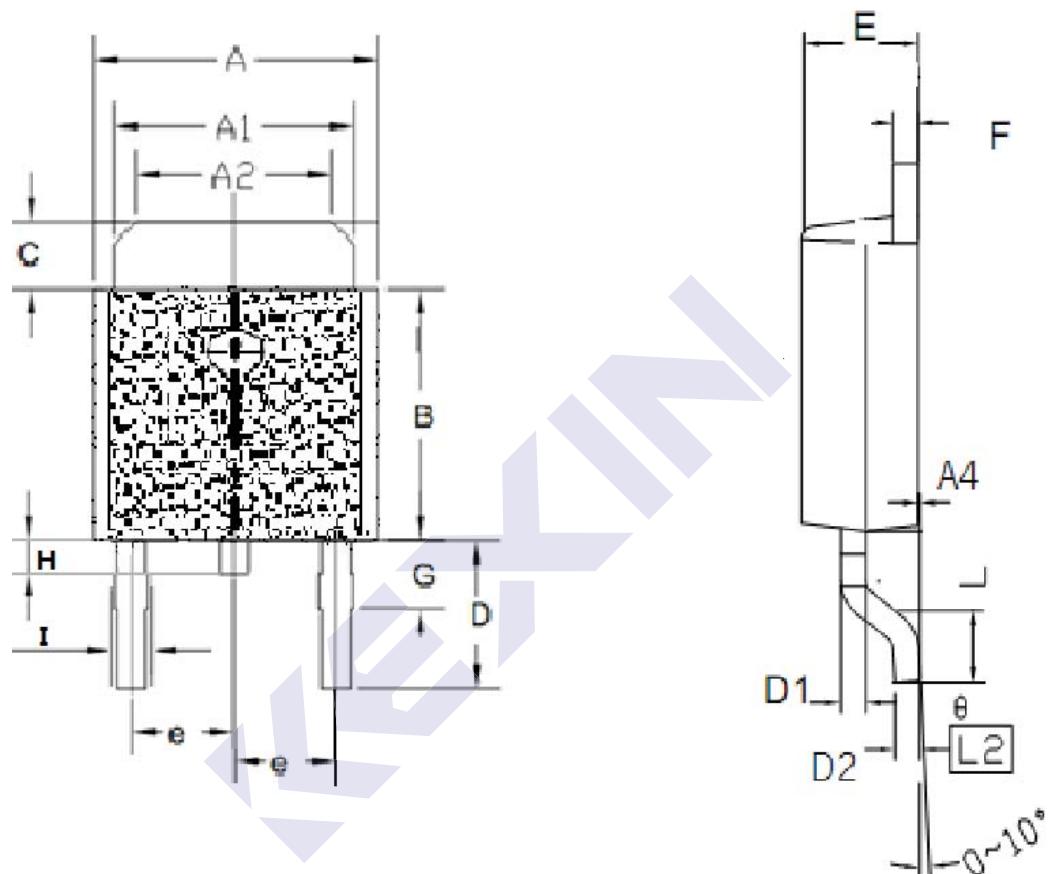
Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

2KK5064

■ Package Dimension

TO-252

Units: mm



Symbol	Min	Max	Symbol	Min	Max
A	6.40	6.60	D	2.90	3.10
A1	5.20	5.40	D1	0.45	0.55
A2	4.40	4.60	D2	0.45	0.55
A3	4.40	4.60	e		2.30
A4	0.00	0.15	E	2.20	2.40
A5	4.65	4.95	F	0.49	0.59
B	6.00	6.20	G		1.70
B1	1.57	1.77	L	1.40	1.60
C	0.90	0.96	$\theta(^{\circ})$	0.00	10.00
I	0.60	0.90	H	0.49	0.52